CLAIMS

1. A method for manufacturing a silicon optical interposer, comprising:

providing a wafer, wherein a silicon optoelectronic device is formed on the wafer by etching for a waveguide, epitaxy, ion implantation, and fabricating a thermode, and the silicon optoelectronic device comprises a passive silicon optoelectronic device and an active silicon optoelectronic device;

depositing a first dielectric layer on a top of the silicon optoelectronic device, and forming a first contact via downward from a top of the first dielectric layer through chemical mechanical polishing, for the active silicon optoelectronic device and/or a thermo-optic device in the passive silicon optoelectronic device;

depositing a second dielectric layer, and forming through silicon vias downward from a top of the second dielectric layer;

depositing a third dielectric layer, and forming, on a top of the third dielectric layer, an electrode corresponding to the thermo-optic device and/or the active silicon optoelectronic device, wherein each electrode corresponds to the first contact via and the through via, and a second contact via and a third contact via are formed downward from a bottom of each electrode, the second contact via is connected to the first contact via, and the third contact via is connected to the through silicon via;

performing chemical mechanical polishing on a top of the structure that has been formed, depositing a fourth dielectric layer, forming a bonding pad opening running through the fourth dielectric layer, and forming a first under micro-bump metal or a first micro-bump, wherein the bonding pad opening is located above the electrode;

grinding the wafer from a back surface to expose the through silicon vias;

depositing a passivation layer on the back surface of the wafer; and

etching the passivation layer to form a passivation layer opening for the through silicon via; and forming a redistribution layer, and a second under micro-bump metal or a second micro-bump in the passivation layer opening, or forming a second under micro-bump metal or a second micro-bump in the passivation layer opening;

wherein a perpendicular distance between each through silicon via and a side, of the silicon optoelectronic device, adjacent to said through silicon via is not less than 1.5 times a diameter of each through silicon via.

2. The method according to claim 1, wherein forming the first contact via downward from the top of the first dielectric layer, forming the through silicon vias downward from the top of the second dielectric layer, or forming the electrode, the second contact via, and the third contact via, comprises:

etching downward from the top of a target dielectric layer, to form a target hole;

depositing an isolation layer on a sidewall and a bottom of the target hole;

coating the target hole electrochemically with a metal, or depositing a metal in the target hole; and

removing the metal and the isolation layer that are on a surface of the target dielectric layer, through chemical mechanical polishing or etching;

wherein in case of forming the first contact via downward from the top of the first dielectric layer, the target dielectric layer is the first dielectric layer, the target hole is a first hole, the metal is a first metal;

wherein in case of forming the through silicon vias downward from the top of the second dielectric layer, the target dielectric layer is the second dielectric layer, the target hole is a second hole, the metal is a second metal;

wherein in case of forming the electrode, the second contact via, and the third contact via,

the target dielectric layer is the third dielectric layer, the target hole is a third hole and a fourth hole, the metal is a third metal; and

etching downward from the top of the target dielectric layer to form the target hole comprises: etching from the top of the third dielectric layer to form electrode grooves, and etching, downward from a bottom of each electrode groove, to form the third hole and the fourth hole.

3. The method according to claim 2, wherein

the metal is copper;

the target hole is filled with the copper through electrochemical coating, and the copper is annealed and subject to chemical mechanical polishing; and

a stop layer is deposited after forming the first contact via and before depositing the second dielectric layer, after forming the through silicon via and before depositing the third dielectric layer, or after forming the electrode groove, the third hole, and the fourth hole and before depositing the fourth dielectric layer.

4. The method according to claim 1, wherein each of the first dielectric layer, the second dielectric layer, the third dielectric layer, and the fourth dielectric layer is formed through plasma enhanced chemical vapor deposition.

5. The method according to claim 2, wherein each of the first hole, the third hole, the fourth hole, and the electrode grooves is formed through dry etching.

6. The method according to claim 1, wherein a grid-type dielectric isolation structure is disposed under the electrode .

7. A method for manufacturing a three-dimensional structure, comprising:

providing a silicon optical interposer manufactured by the method according to any one of claims 1 to 6; and

bonding the silicon optical interposer to an electronic chip or an optoelectronic chip via the first under micro-bump metal or the first micro-bump;

wherein the method further comprises:

bonding the silicon optical interposer to a silicon interposer via the redistribution layer and the second under micro-bump metal or the second micro-bump, or via the second under micro-bump metal or the second micro-bump; and connecting the silicon

optical interposer to a package substrate via a third under micro-bump metal or a third micro-bump arranged on a back surface of the silicon interposer; or

connecting the silicon optical interposer to a package substrate directly via the redistribution layer and the second under micro-bump metal or second micro-bump of the silicon optical interposer, or via the second under micro-bump metal or the second micro-bump silicon optical interposer of the silicon optical interposer.

8. A method for integrating a surface-electrode ion trap and a silicon optoelectronic device, comprising:

providing a wafer;

forming a grating and a silicon structure on the wafer, wherein the silicon structure is formed at a top of the wafer through photolithography and etching, and the silicon structure is subject to ion implantation and annealing;

depositing a first dielectric layer, etching the first dielectric layer above the silicon structure to form an epitaxy opening, growing silicon or germanium through epitaxy on a top of the silicon structure via the epitaxy opening, and performing ion implantation and annealing on the silicon or the germanium, to form a silicon single-photon avalanche detector or a silicon-based germanium single-photon avalanche detector;

depositing a second dielectric layer, and forming a first contact via downward from a top of the second dielectric layer through etching and performing chemical mechanical polishing, for the silicon single-photon avalanche detector or the silicon-based germanium single-photon avalanche detector of a surface-incident type;

depositing a third dielectric layer, and forming through silicon vias downward from a top of the third dielectric layer;

depositing a fourth dielectric layer, and forming an electrode on a top of the fourth dielectric layer, wherein the electrode comprises a first electrode corresponds to the silicon single-photon avalanche detector or the silicon-based germanium single-photon avalanche detector and a second electrode for the surface-electrode ion trap, each first electrode corresponds to the first contact via and the through silicon via, each second electrode corresponds to the through silicon via, a second contact via is formed downward from a

bottom of each first electrode, the second contact via is connected to the first contact via, a third contact via is formed downward from the bottom of each first electrode and a bottom of each second electrode, and the third contact via is connected to the through silicon via;

grinding the wafer from a back surface to expose the through silicon vias;

depositing a passivation layer on the back surface of the wafer; and

etching the passivation layer to form a passivation layer opening for the through silicon via; and forming a redistribution layer, and a first under micro-bump metal or a first micro-bump in the passivation layer opening, or forming a first under micro-bump metal or a first micro-bump in the passivation layer opening;

wherein forming the grating comprises forming a silicon grating at the top of the wafer through photolithography and etching; or

wherein:

forming the grating comprises: depositing a fifth dielectric layer and a silicon nitride layer sequentially, and forming a silicon nitride grating at a top of the silicon nitride layer through photolithography and etching; and

the fifth dielectric layer above the silicon structure is further etched to form the epitaxy opening; and

wherein a perpendicular distance between each through silicon via and a side, of the silicon single-photon avalanche detector or the silicon-based germanium single-photon avalanche detector, adjacent to said through silicon via is not less than 1.5 times a diameter of each through silicon via.

9. The method according to claim 8, wherein forming the first contact via downward from the top of the second dielectric layer, forming the through silicon vias downward from the top of the third dielectric layer, or forming the electrode, the second contact via, and the third contact via, comprises:

etching downward from the top of a target dielectric layer, to form a target hole;

depositing an isolation layer on a sidewall and a bottom of the target hole;

coating the target hole electrochemically with a metal, or depositing a metal in the target hole;

removing the metal and the isolation layer that are on a surface of the target dielectric layer, through chemical mechanical polishing or etching;

wherein in case of forming the first contact via downward from the top of the first dielectric layer, the target dielectric layer is the second dielectric layer, the target hole is a first hole, the metal is a first metal;

wherein in case of forming the through silicon vias downward from the top of the second dielectric layer, the target dielectric layer is the third dielectric layer, the target hole is a second hole, the metal is a second metal;

wherein in case of forming the electrode, the second contact via, and the third contact via,

the target dielectric layer is the fourth dielectric layer, the target hole is a third hole and a fourth hole, the metal is a third metal; and

etching downward from the top of the target dielectric layer to form the target hole comprises: etching from the top of the fourth dielectric layer to form electrode grooves, and etching, downward from a bottom of each electrode groove, to form the third hole and the fourth hole.

10. The method according to claim 9, wherein:

the metal is copper;

the target hole is filled with the copper through electrochemical coating, and the copper is annealed and subject to chemical mechanical polishing;

a stop layer is deposited after forming the first contact via and before depositing the third dielectric layer, or after forming the through silicon via and before depositing the fourth dielectric layer.

11. The method according to claim 8, wherein each of the first dielectric layer, the

second dielectric layer, the third dielectric layer, and the fourth dielectric layer is formed through plasma enhanced chemical vapor deposition.

12. The method according to claim 9, wherein each of the first hole, the third hole, the fourth hole, and the electrode grooves is formed through dry etching.

13. The method to claim 8, wherein a grid-type dielectric isolation structure is disposed under the electrode.

14. A method for manufacturing a three-dimensional structure, comprising:

bonding an integrated structure manufactured by the method according to any one of claims 8 to 13 to a silicon interposer via the redistribution layer and the first under micro-bump metal or the first micro-bump, or via the first under micro-bump metal or the first micro-bump; and connecting the silicon optical interposer to a package substrate, via a second under micro-bump metal or a second micro-bump arranged on a back surface of the silicon optical interposer, or via a lead; or

connecting the integrated structure to a package substrate directly via the redistribution layer and the first under micro-bump metal or first micro-bump of the integrated structure.

15. An integrated structure of a surface-electrode ion trap and a silicon optoelectronic device, comprising:

a wafer, wherein a grating and a silicon structure are located on the wafer, the silicon structure is formed at a top of the wafer through photolithography and etching, and the silicon structure is subject to ion implantation and annealing;

a first dielectric layer formed on the above-formed structure, wherein the first dielectric layer above the silicon structure is etched to form epitaxy openings, silicon or germanium is grown through epitaxy on a top of the silicon structure via the epitaxy opening, and ion implantation and annealing is performed to form silicon single-photon avalanche detectors or the silicon-based germanium single-photon avalanche detectors;

a second dielectric layer formed on the above-formed structure, wherein first contact vias are formed downward from a top of the second dielectric layer for the silicon single-photon avalanche detectors or the silicon-based germanium single-photon avalanche detectors of a surface-incident type;

a third dielectric layer formed on the above-formed structure, wherein through silicon vias are formed downward from a top of the third dielectric layer;

a fourth dielectric layer formed on the above-formed structure, wherein electrodes are formed on a top of the fourth dielectric layer, the electrode comprises a first electrode corresponds to the silicon single-photon avalanche detector or the silicon-based germanium single-photon avalanche detector and a second electrode for the surface-electrode ion trap, each first electrode corresponds to the first contact via and the through silicon via, each second electrode corresponds to the through silicon via, a second contact via is formed downward from a bottom of each first electrode, the second contact via is connected to the first contact via, a third contact via is formed downward from the bottom of each first electrode and a bottom of each second electrode, and the third contact via is connected to the through silicon via; and

a first passivation layer deposited on a back surface of the wafer, wherein the back surface is grinded to expose the through silicon vias, and passivation layer openings for the through silicon vias are formed by etching the passivation layer, and a first under micro-bump metal or a first micro-bump is formed in each passivation layer opening, or a first under micro-bump metal or a first micro-bump is formed on a redistribution layer in each passivation layer opening;

wherein the grating comprises at least one of a silicon grating or a silicon nitride grating;

wherein the silicon grating is formed at the top of the wafer through photolithography and etching;

wherein the silicon nitride grating is formed at a top of a silicon nitride layer through photolithography and etching, the integrated structure further comprises a fifth dielectric layer and the silicon nitride layer that are sequentially located between the wafer and the first dielectric layer, and the fifth dielectric layer is further etched to form the epitaxy openings; and

wherein a perpendicular distance between each through silicon via and a side, of the silicon single-photon avalanche detector or the silicon-based germanium single-photon avalanche detector, adjacent to said through silicon via is not less than 1.5 times a diameter of each through silicon via.

16. The integrated structure according to claim 15, wherein the first contact vias, the through silicon vias, or a combination of the electrodes, the second contact vias and the third contact vias comprises:

a target hole, arranged in a target dielectric layer;

an isolation layer, deposited on a bottom and a sidewall of the target hole; and

a metal structure, with which the target hole with the isolation layer is electrochemically coated, or which is deposited in the target hole with the isolation layer;

wherein in case of the first contact vias, the target dielectric layer is the second dielectric layer, the target hole is a first hole, the metal structure is a first metal structure;

wherein in case of the through silicon vias, the target dielectric layer is the third dielectric layer, the target hole is a second hole, the metal structure is a second metal structure;

wherein in case of the combination of the electrodes, the second contact vias and the third contact vias,

the target dielectric layer is the fourth dielectric layer, the target hole is a third hole and a fourth hole, the metal structure is a third metal structure; and

the top of the fourth dielectric layer is etched to form electrode grooves, and a bottom of each electrode groove is etched to form the third hole and the fourth hole.

17. The integrated structure according to claim 16, wherein:

the metal structure is a copper structure;

the target hole is filled with copper through electrochemical coating, and the copper is annealed and subject to chemical mechanical polishing, to form the copper structure; and

a stop layer is deposited after forming the first contact via and before depositing the third

dielectric layer, or after forming the through silicon vias and before depositing the fourth dielectric layer.

18. The integrated structure according to claim 17, wherein a second passivation layer is deposited in the electrode grooves, the third hole, and the fourth hole, after the third isolation layer and the third metal structure are sequentially formed.

19. The integrated structure according to claim 16, wherein each of the first isolation layer, the second isolation layer, and the third isolation layer is made of Ta, TaN, or a combination of Ta and TaN.

20. The integrated structure according to claim 15, wherein each of the first dielectric layer, the second dielectric layer, the third dielectric layer, and the fourth dielectric layer is a dielectric layer of silicon dioxide.

21. The integrated structure according to claim 17, wherein the stop layer is made of silicon nitride.

22. The integrated structure according to claim 15, wherein:

a perpendicular distance between central axes of every two adjacent through silicon vias is not less than 3 times the diameter of each through silicon via.

23. The integrated structure according to claim 15, wherein a grid-type dielectric isolation structure is disposed under the electrode.

24. A three-dimensional structure, comprising:

the integrated structure according to any one of claims 15 to 23;

and the three-dimensional structure further comprises:

a silicon interposer and a package substrate, wherein the silicon interposer is bonded to the first under micro-bump metal or the first micro-bump of the integrated structure, and the package substrate is bonded to the silicon interposer via the second under micro-bump metal or a second micro bump arranged on the back surface of the silicon interposer, or bonded to the silicon interposer via a lead; or

a package substrate, directly connected to the first under micro-bump metal or the first micro-bump of the integrated structure.

25. The three-dimensional structure according to claim 24, wherein the second under micro-bump metal is made of Cu/Ni/Au, and the second micro-bump is made of Cu/Ni/SnAg.